MMBT6428LT1G, MMBT6429LT1G

Amplifier Transistors

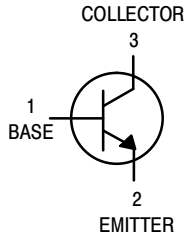
NPN Silicon

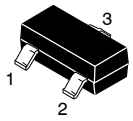
ON Semiconductor®

http://onsemi.com

Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant





SOT−23 (TO−236)
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	6428LT1	6429LT1	Unit
Collector−Emitter Voltage	V_{CEO}	50	45	Vdc
Collector−Base Voltage	V_{CBO}	60	55	Vdc
Emitter−Base Voltage	V_{EBO}	6.0		Vdc
Collector Current − Continuous	I_C	200		mAdc

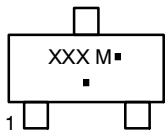
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

MARKING DIAGRAM



XXX = Specific Device Code
MMBT6428LT1 − 1KM
MMBT6429LT1 − M1L
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT6428LT1G	SOT−23 (Pb−Free)	3000 Tape & Reel
MMBT6429LT1G	SOT−23 (Pb−Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage		$V_{(BR)CEO}$			Vdc
(I_C = 1.0 mAdc, I_B = 0)	MMBT6428		50	–	
(I_C = 1.0 mAdc, I_B = 0)	MMBT6429		45	–	
Collector – Base Breakdown Voltage		$V_{(BR)CBO}$			Vdc
(I_C = 0.1 mAdc, I_E = 0)	MMBT6428		60	–	
(I_C = 0.1 mAdc, I_E = 0)	MMBT6429		55	–	
Collector Cutoff Current		I_{CES}			μAdc
(V_{CE} = 30 Vdc)			–	0.1	
Collector Cutoff Current		I_{CBO}			μAdc
(V_{CB} = 30 Vdc, I_E = 0)			–	0.01	
Emitter Cutoff Current		I_{EBO}			μAdc
(V_{EB} = 5.0 Vdc, I_C = 0)			–	0.01	
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			–
(I_C = 0.01 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250	–	
	MMBT6429		500	–	
(I_C = 0.1 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250	650	
	MMBT6429		500	1250	
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250	–	
	MMBT6429		500	–	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	MMBT6428		250	–	
	MMBT6429		500	–	
Collector – Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 0.5 mAdc)			–	0.2	
(I_C = 100 mAdc, I_B = 5.0 mAdc)			–	0.6	
Base – Emitter On Voltage		$V_{BE(on)}$			Vdc
(I_C = 1.0 mAdc, V_{CE} = 5.0 mAdc)			0.56	0.66	
SMALL – SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product		f_T			MHz
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)			100	700	
Output Capacitance		C_{obo}			pF
(V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)			–	3.0	
Input Capacitance		C_{ibo}			pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)			–	8.0	

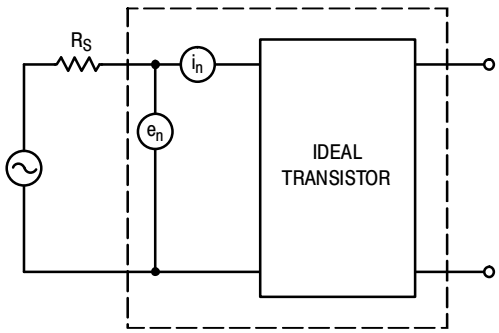


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

NOISE VOLTAGE

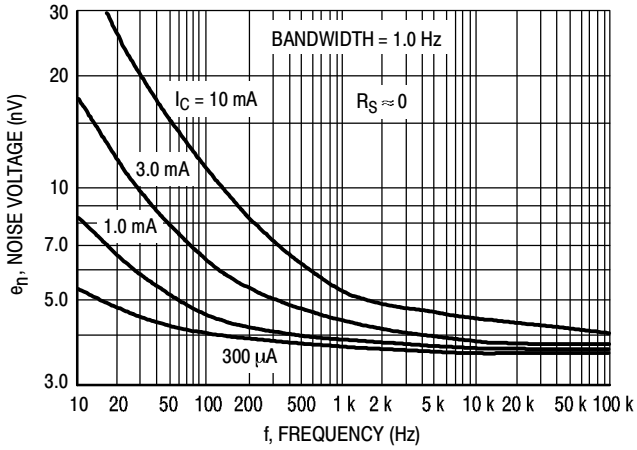


Figure 2. Effects of Frequency

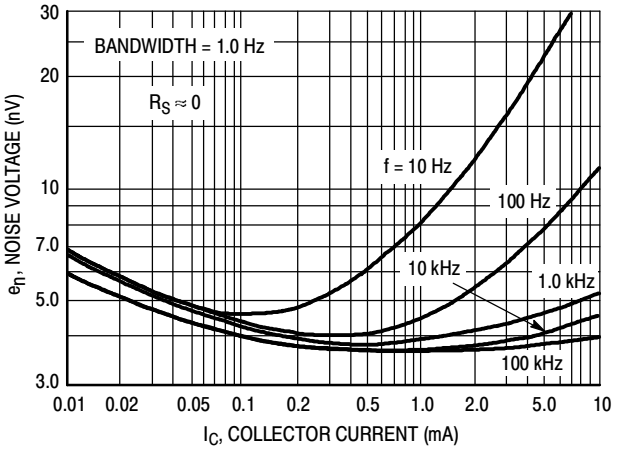


Figure 3. Effects of Collector Current

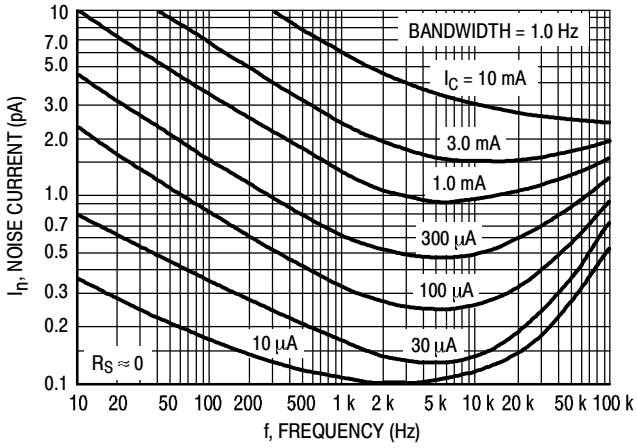


Figure 4. Noise Current

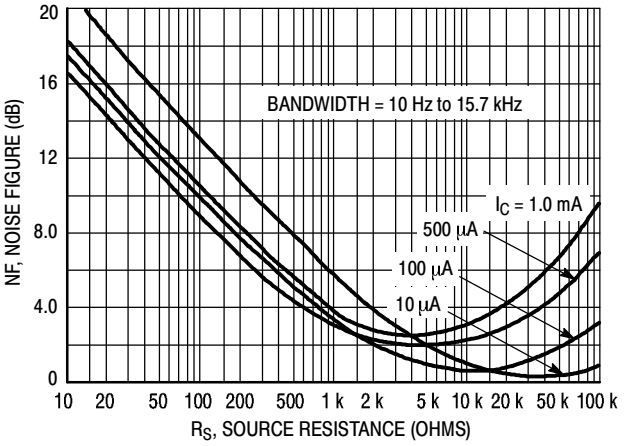


Figure 5. Wideband Noise Figure

100 Hz NOISE DATA

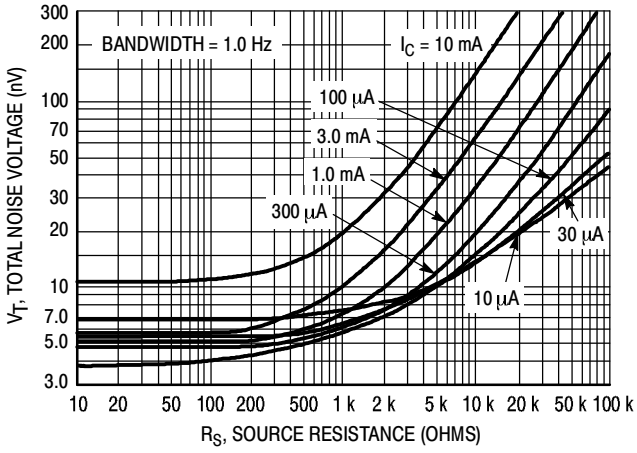


Figure 6. Total Noise Voltage

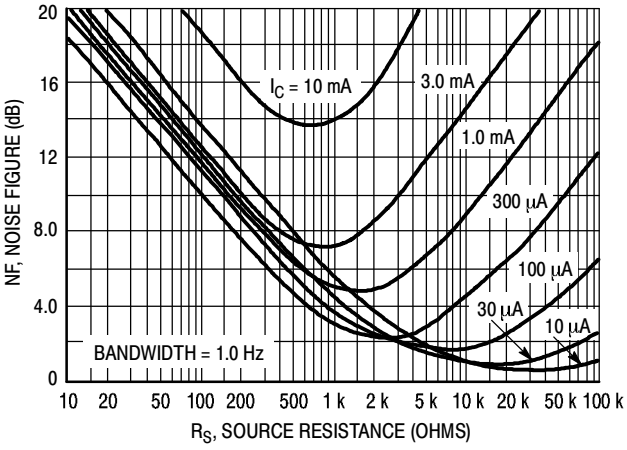


Figure 7. Noise Figure

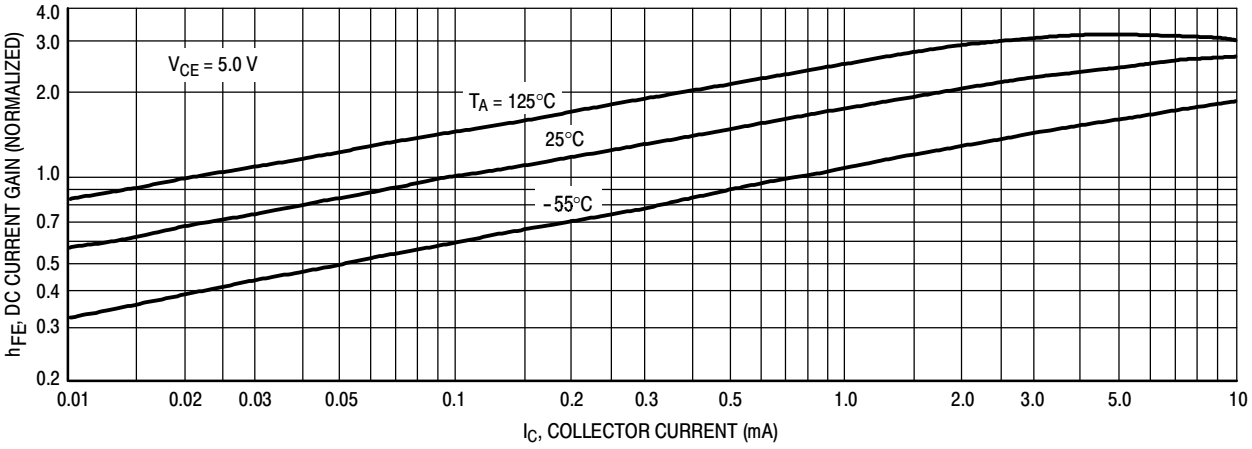


Figure 8. DC Current Gain

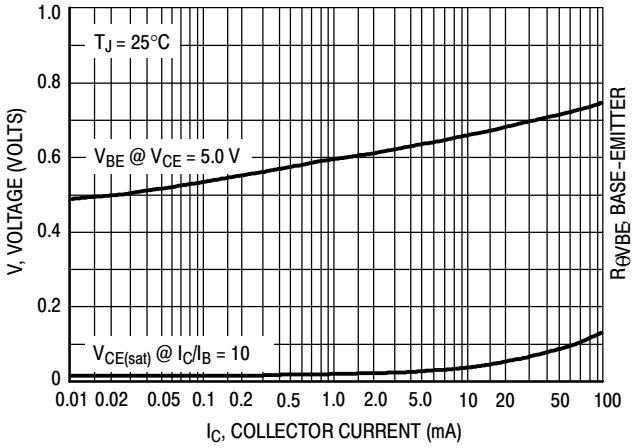


Figure 9. "On" Voltages

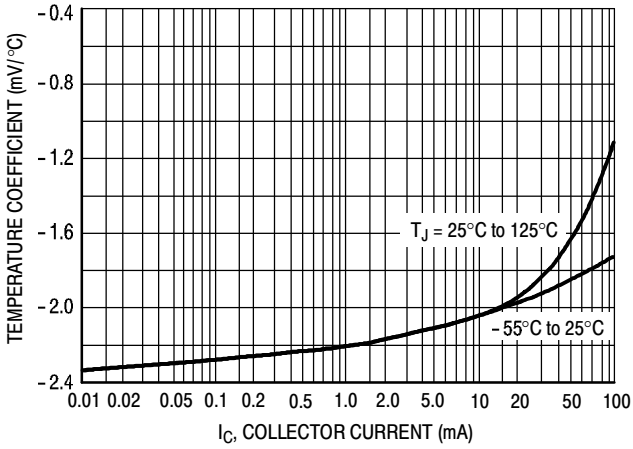


Figure 10. Temperature Coefficients

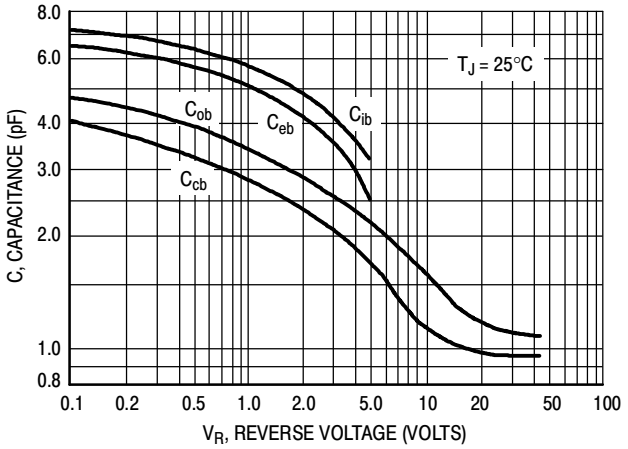


Figure 11. Capacitance

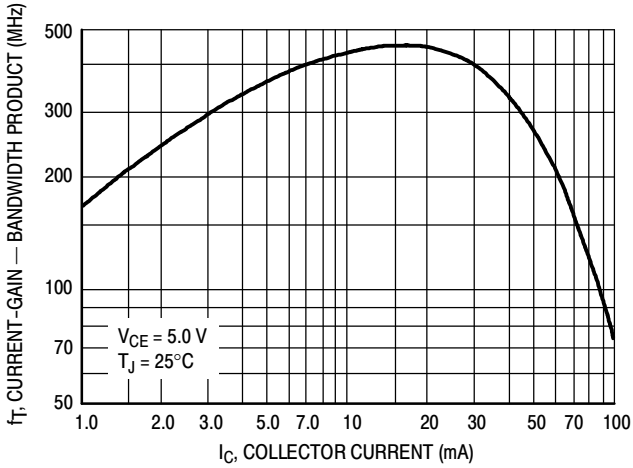
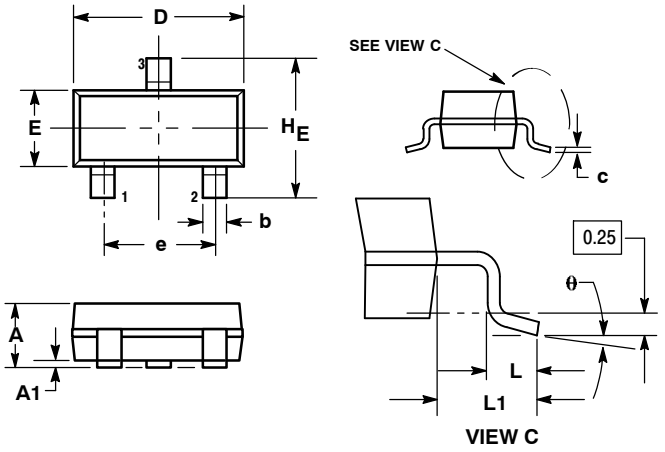


Figure 12. Current–Gain — Bandwidth Product

MMBT6428LT1G, MMBT6429LT1G

PACKAGE DIMENSIONS

SOT−23 (TO236)
CASE 318−08
ISSUE AN

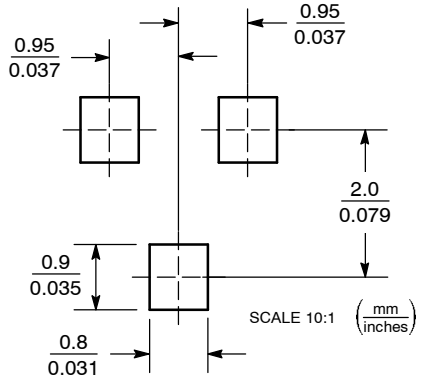


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01 THRU −07 AND −09 OBSOLETE, NEW STANDARD 318−08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT



PUBLICATION ORDERING INFORMATION

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